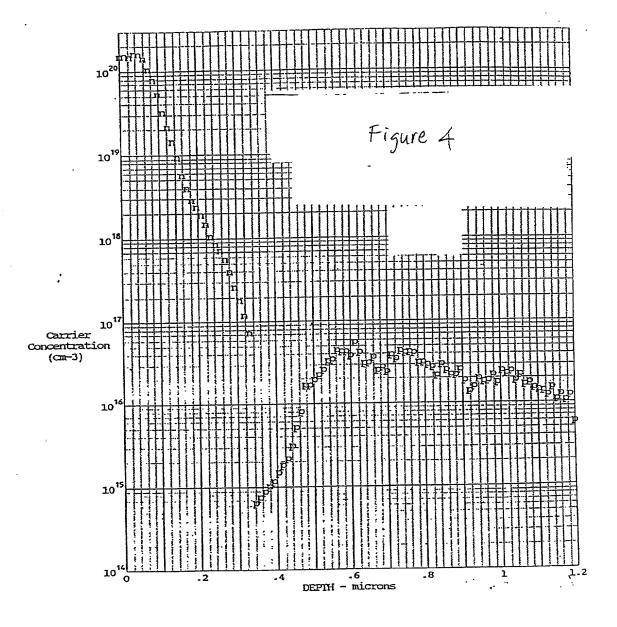
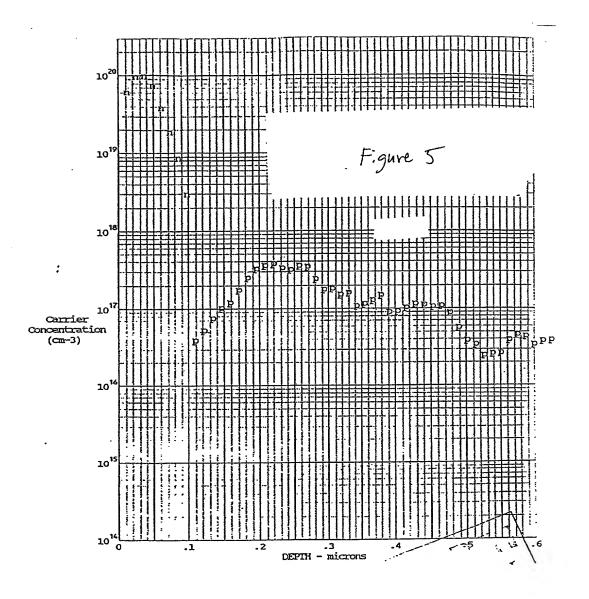


FIG. 3

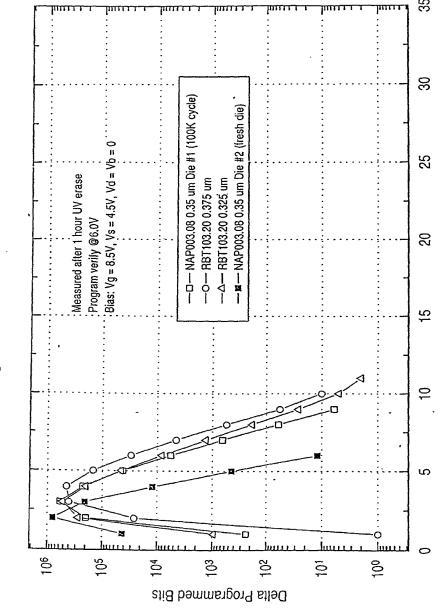




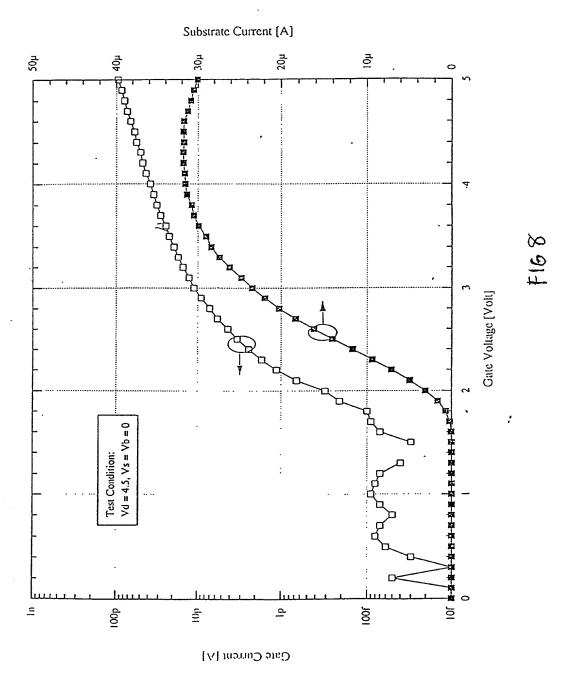
——— NAP003.08 0.35 µm Die #1 (100k cycle) --- NAP003.08 0.35 µm Die #2 (Fresh die) 8 Measured after 1 hour UV erase Program verify @6.0V : Bias: Vg = 8.5V, Vd = 4.5V, Vs = Vb = 0 Drain Side Program Rate Distribution After UV Erase —o— RBT 103.20 0.375 µm 25 Number of Programming Pulse (1μs/pulse) 20 . 으 S 106 105 103 100 104 105 5 Delta Programmed Bits

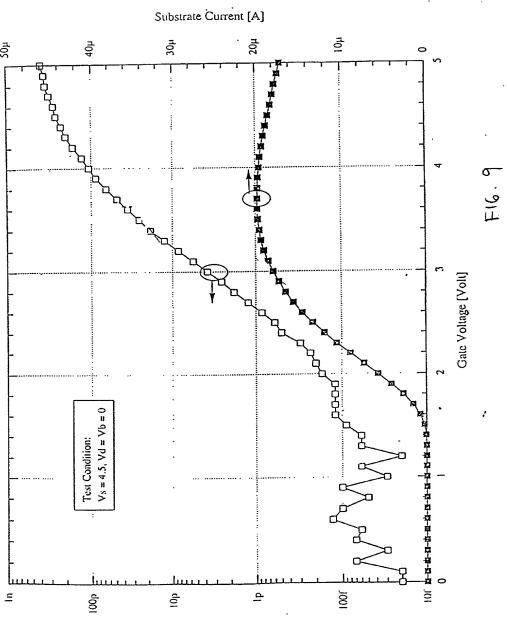
35

Source Side Program Rate Distribution After UV Erase



Number of Programming Pulse (1μs/pulse)





. Gate Current [A]